

元素	熔點°C	密度 gm/cm ³	Boat/Crucible	應用 /(operation) note
Ag	961	10.5	W, Ta, Mo, Al ₂ O ₃	Highest reflectance mirrors visible to IR.
Al	660	2.7	Bn-TiB ₂ , W	Conductive lines. Front surfaced mirrors, reflectors
AlF ₃	1257 sublimes	2.9	W, Mo, Ta	Not affected by water. Good mechanical strength
Al ₂ O ₃	2015	3.96	W	Al mirror protection. UV laser ARC and high reflectors.
AZOY 2/98 wt%	1975	5.66		Transparent conductive film
Au	1063	19.3	W, Mo	Contact layer. High reflecting films for front surface mirror in IR laser system.
B	2180	2.35		(carbide with crucible, cool slow)
Ba	714	3.58	W, Mo, Ta	(wets without alloying, reacts with ceramic)
BaF ₂	1280	4.89	W, Mo, Ta	
BaO	1923	5.72	Pt	
Be	1278	1.85	W, Mo, Ta	(Toxic) Semiconductor junctions.(Wets W. Mo. Ta)
Bi ₂ O ₃	820	8.9	Pt, Mo	(Vaportoxic) Beam splitter
Bo ₂ Te ₃	585	7.9	W, Mo	Magneto-optic film.(by co-evaporation)
Ca	850	1.55	W	Corrodes in air
CaF ₂	1403	3.18	Mo, Ta, W	Low index UV-IR. Anti-Reflection Coating on glass
CdS	1477	4.82	Mo, W	(aperture cover required)

CeF ₃	1460	6.16	W, Mo, TA	(preheat to outgas)
元素	熔點℃	密度 gm/cm ³	Boat/Crucible	應用 /(operation) note
CeO ₂	2600	7.13	W	
Co	1492	8.9	W/Al ₂ O ₃ , W	Ferromagnetic thin film. (alloys with refractories)
Cr	1890	7.19	W, Cr	Beam splitting film. Mirrors. Adhesion film on glass for printed circuits
Cr ₂ O ₃	2435	5.2	W	hard binding layer. (Decompose to lower oxides, reoxidized @100°C)
Cr-SiO			W	Resistor films (by flash evaporation)
Cu	1083	8.93	W, Mo, Ta	IR reflector. Contacts
Fe	1536	7.87	W	Photo mask. (attacks W)
Ga	30	5.9		(alloys with refractories)
GaN	800 sublimes	6.1		(evaporate Ga in 10-3 N ₂)
Ge	958	5.32	W, Mo, Ta	High index film in IR filters.
GeO ₂	1086	6.2	Mo, Ta, W	Dielectric, protective film
Hf	2230	13.28		
HfO ₂	2812	9.68	W	IR mirror overcoat, UV laser multilayers, emitter wire coating. (high damage threshold 0.35μ)
In	156	7.31	W, Mo	Transistor contacts. Solder joints. (wets W and Cu, Ta or Mo liner required)
ITO(90/10 wt%)	~1900	1.17	W, Pt	Transparent conductive film.
La	920	6.17	Ta	(Films burn in air if scrape)

LaF3	1490	5.94	Mo, Ta	(preheat to outgas)
元素	熔點℃	密度 gm/cm ³	Boat/Crucible	應用 /(operation) note
LiF	845	2.6	Ta, Mo, W	(preheat to outgas)
Mg	650	1.74	W, Mo, Ta	Diffusion with Bi on glass to form ferromagnetic film.
MgF2	1261	3.2	W, Mo, Ta	ARC multiayers. (reacts with W)
MgO	2852	3.58	W	Insulator. High Temp. dielectric.
Mn	1245	7.43	W, Mo, Ta	Semiconductor contacts. Adhesion film.
Mo	2610	10.22		Semiconductor contacts. Hard, somooth film
Nb	2468	8.57		Anodic film for rectification.
Ni	1453	8.91	W/Al2O3, W	Durable mirrors. Adhesion layer.(alloy with refractories)
NiCr(80/20 wt%)	1450	8.4	W, Ta	Thin film resistor. Good adhesion on non-metals.(alloy with refractories)
Pb	328	11.34	W, Ta, Mo	(Toxic, rate control important)
PbF2	855	8.24	W, Pt, Ta	(Toxic)Dielectric interference filter for UV
Pd	1552	12.02	W	(alloy with refractoriores, fine wire-rapid evaporationsuggested)
Pr2O3	2200	7.07	W	wide-band Vis AR coating (Reactive to radio frequency)
Pt	1769	21.45	W	(alloy with metal. liner, fine wire will self evaporate)